

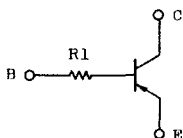
RN2010, 2011

SWITCHING, INVERTER CIRCUIT, INTERFACE CIRCUIT
AND DRIVER CIRCUIT APPLICATIONS.

FEATURES:

- With Built-in Bias Resistors
- Simplify Circuit Design
- Reduce a Quantity of Parts and Manufacturing Process
- Complementary to RN1010, RN1011

EQUIVALENT CIRCUIT



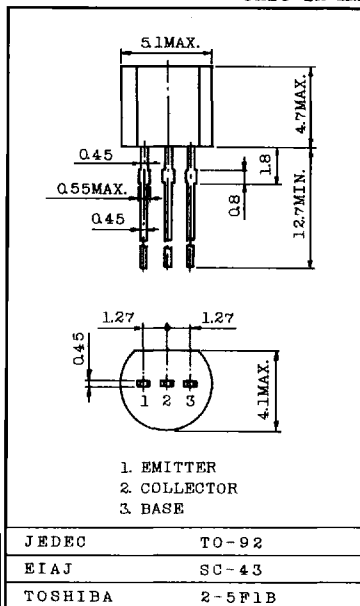
MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CE0}	-50	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current	I _C	-100	mA
Collector Power Dissipation	P _C	400	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CB0}	V _{CB} =-50V, I _E =0	-	-	-100	nA
Emitter Cut-off Current	I _{EB0}	V _{EB} =-5V, I _C =0	-	-	-100	nA
DC Current Gain	h _{FE}	V _{CE} =-5V, I _C =-1mA	120	-	400	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-5mA, I _B =-0.25mA	-	-0.1	-0.3	V
Transition Frequency	f _T	V _{CE} =-10V, I _C =-5mA	-	200	-	MHz
Collector Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz	-	3	6	pF
Input Resistor	RN2010	R1	3.29	4.7	6.11	kΩ
	RN2011		7	10	13	

Unit in mm



Weight : 0.21g

